IXYS

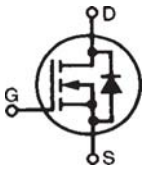
Preliminary Technical Information

High Voltage Power MOSFET

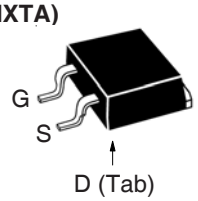
IXTA1N200P3HV
IXTH1N200P3HV
IXTH1N200P3

V_{DSS} = 2000V
I_{D25} = 1.0A
$R_{DS(on)}$ ≤ 40Ω

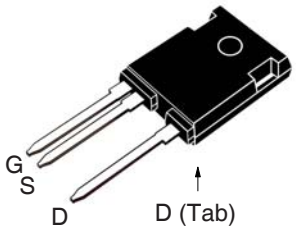
N-Channel Enhancement Mode



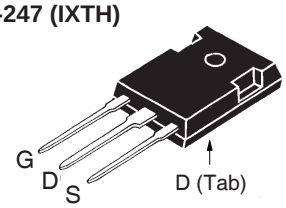
TO-263HV (IXTA)



TO-247HV (IXTH)



TO-247 (IXTH)



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	2000	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	2000	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	1.0	A
I_{D110}	T_C = 110°C	0.6	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	3.0	A
P_D	T_C = 25°C	125	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F_C	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
M_d	Mounting Torque (TO-247/HV)	1.13/10	Nm/lb.in
Weight	TO-263HV	2.5	g
	TO-247/HV	6.0	g

G = Gate D = Drain
S = Source Tab = Drain

Features

- High Blocking Voltage
- High Voltage Packages

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	2000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.0		4.0	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			5	μA
	T_J = 125°C			100	μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5A, Note 1			40	Ω

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 50V, I_D = 0.5A, Note 1	0.4	0.7		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		646		pF
C_{oss}			50		pF
C_{rss}			17		pF
$t_{d(on)}$	**Resistive Switching Times**		16		ns
t_r	V_{GS} = 10V, V_{DS} = 1kV, I_D = 0.5 • I_{D25}		26		ns
$t_{d(off)}$	R_G = 5Ω (External)		37		ns
t_f			80		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 1kV, I_D = 0.5 • I_{D25}		23.5		nC
Q_{gs}			3.1		nC
Q_{gd}			13.3		nC
R_{thJC}				1.0	°C/W
R_{thCS}	TO-247		0.21		°C/W

Source-Drain Diode

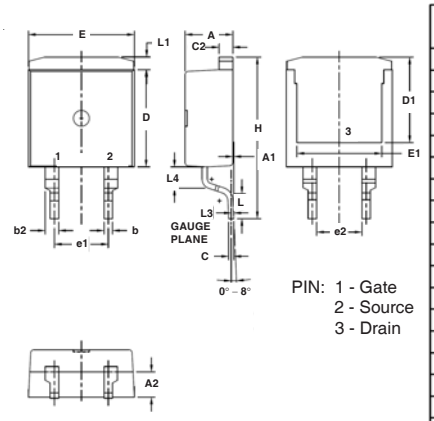
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			1	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			4	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 1A, -di/dt = 100A/μs, V_R = 100V		2.3		μs

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

PRELIMANARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

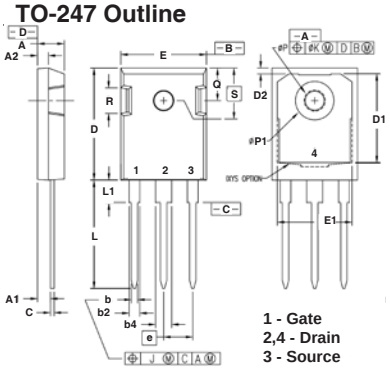
TO-263HV Outline



PIN: 1 - Gate
2 - Source
3 - Drain

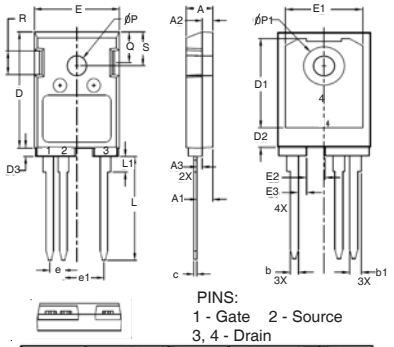
SYM	INCHES MIN	INCHES MAX	MILLIMETER MIN	MILLIMETER MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC		5.08 BSC	
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC		0.254 BSC	
(L4)	.071	.087	1.80	2.20

TO-247 Outline



Dim.	Millimeter min	Millimeter max	Inches min	Inches max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

TO-247HV Outline



PINS:
1 - Gate 2 - Source
3, 4 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100 BSC		2.54 BSC	
e1	.300 BSC		7.62 BSC	
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
øP	.138	.142	3.50	3.60
øP1	.272	.280	6.90	7.10
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30
S	.240	.248	6.10	6.30

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 1. Output Characteristics @ T_J = 25ºC

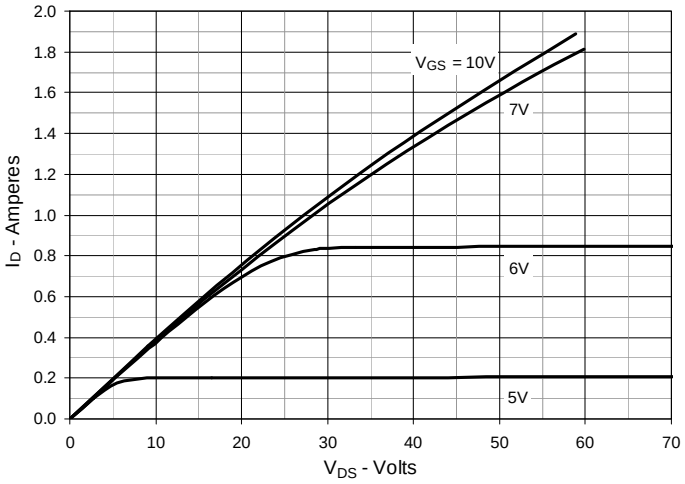


Fig. 2. Output Characteristics @ T_J = 125ºC

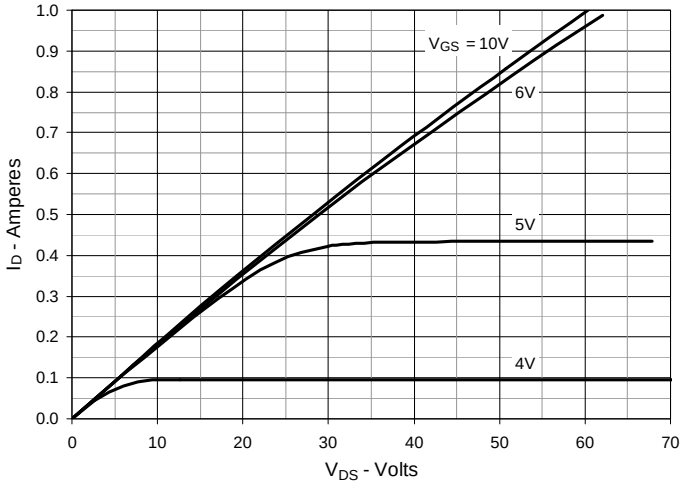


Fig. 3. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Junction Temperature

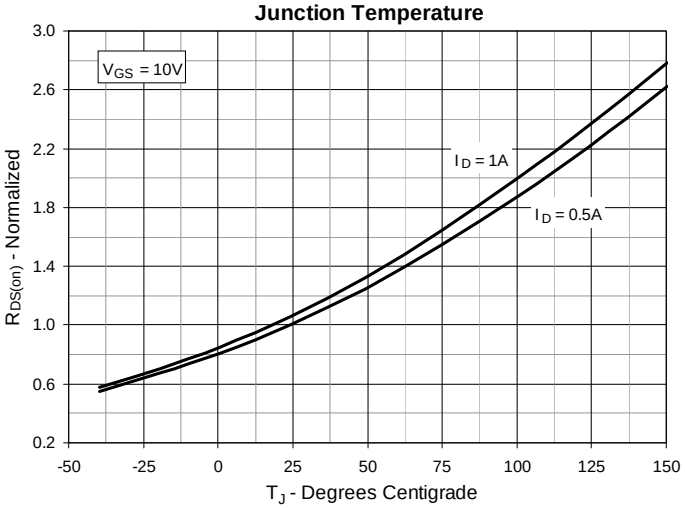


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Drain Current

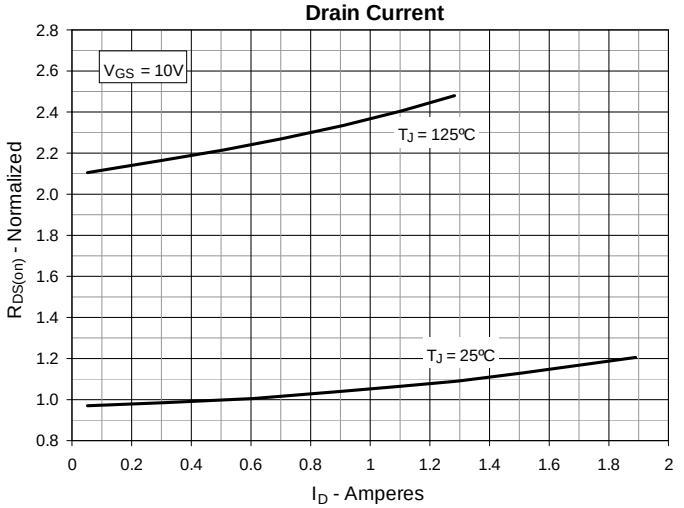


Fig. 5. Maximum Drain Current vs. Case Temperature

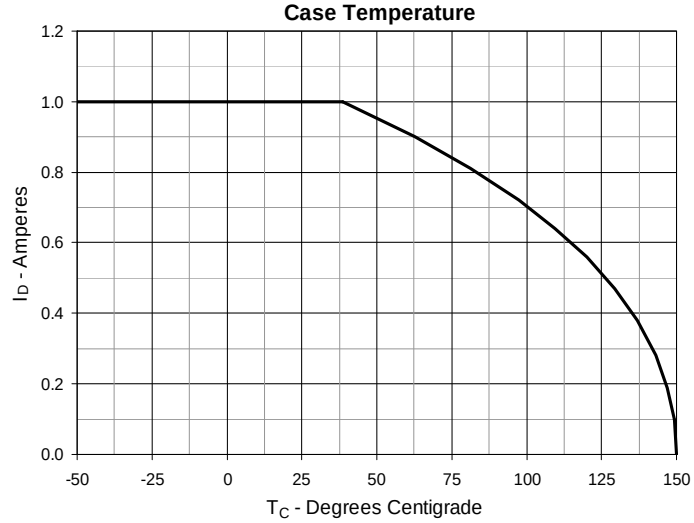


Fig. 6. Input Admittance

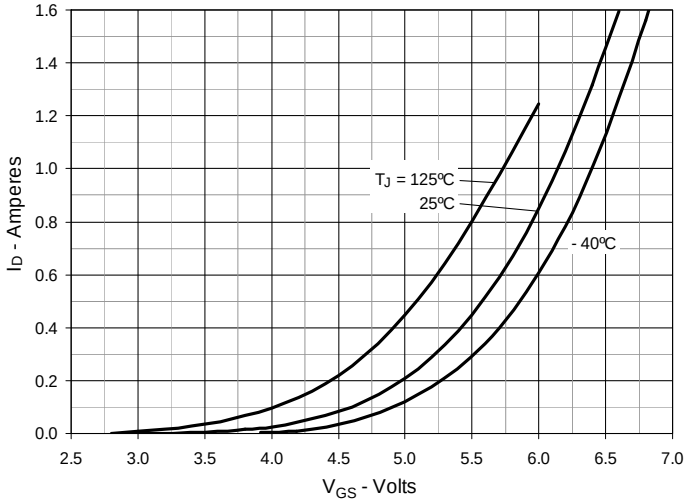


Fig. 7. Transconductance

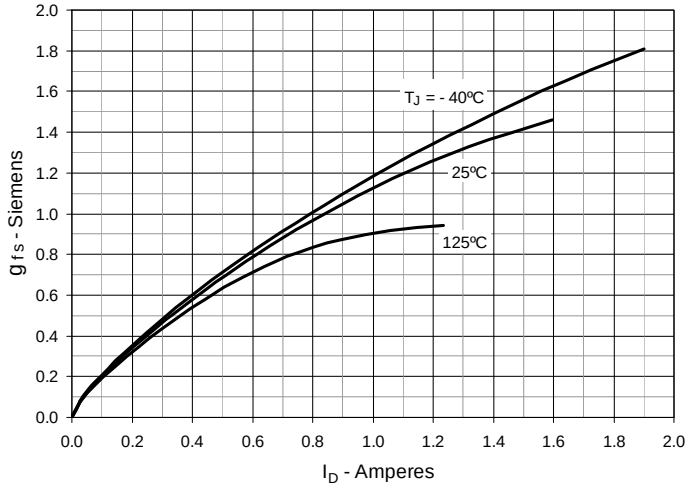


Fig. 8. Forward Voltage Drop of Intrinsic Diode

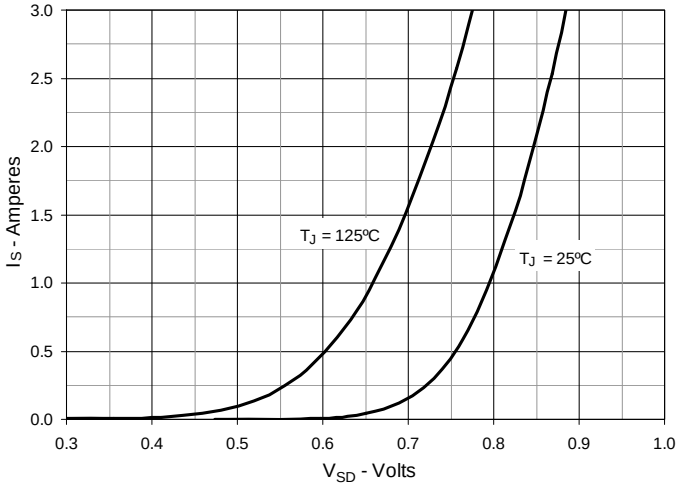


Fig. 9. Gate Charge

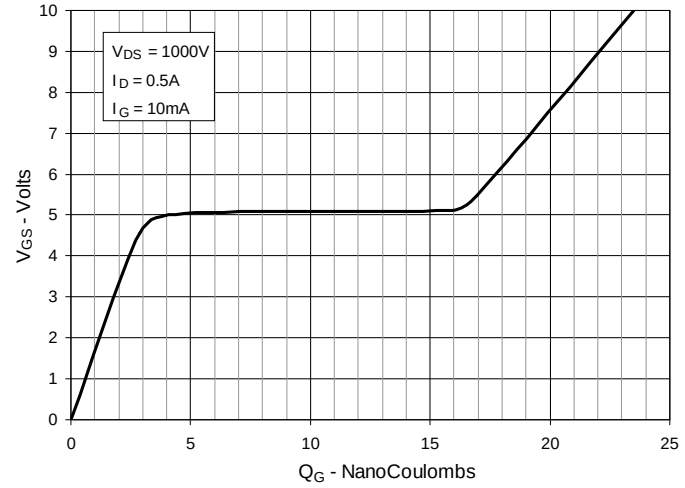


Fig. 10. Capacitance

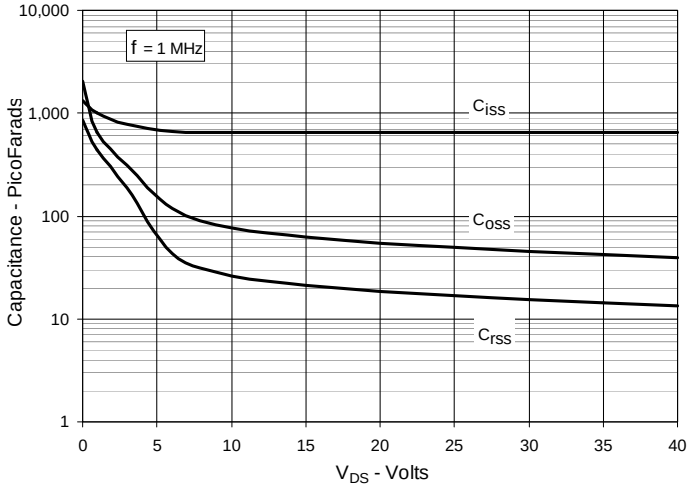


Fig. 11. Maximum Transient Thermal Impedance

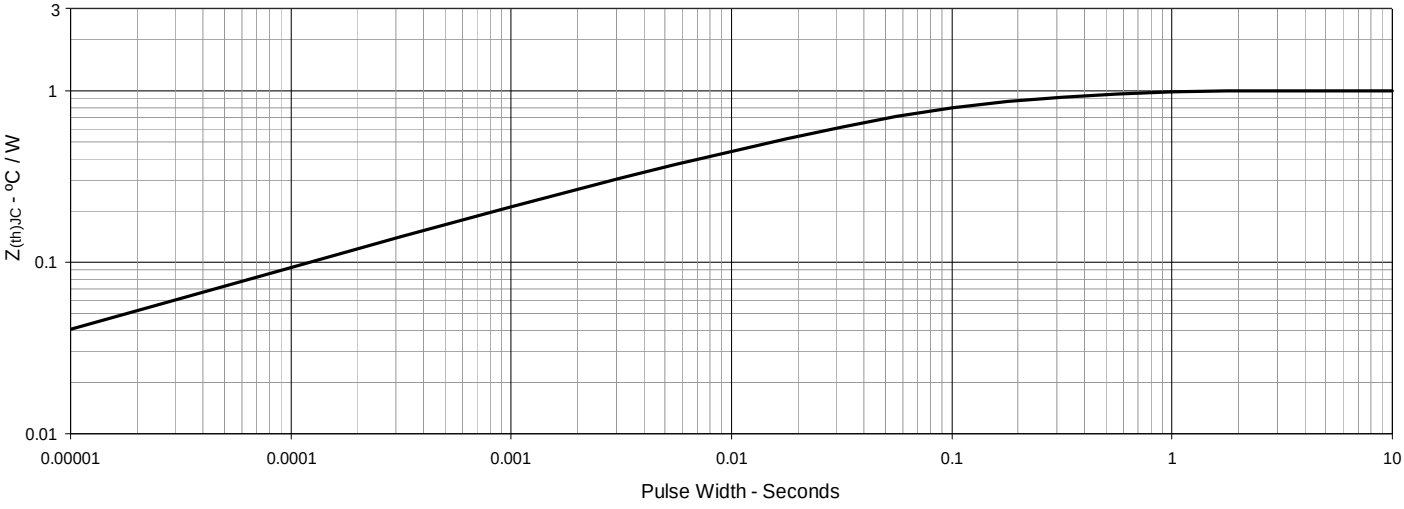


Fig. 12. Forward-Bias Safe Operating Area @ T_C = 25ºC

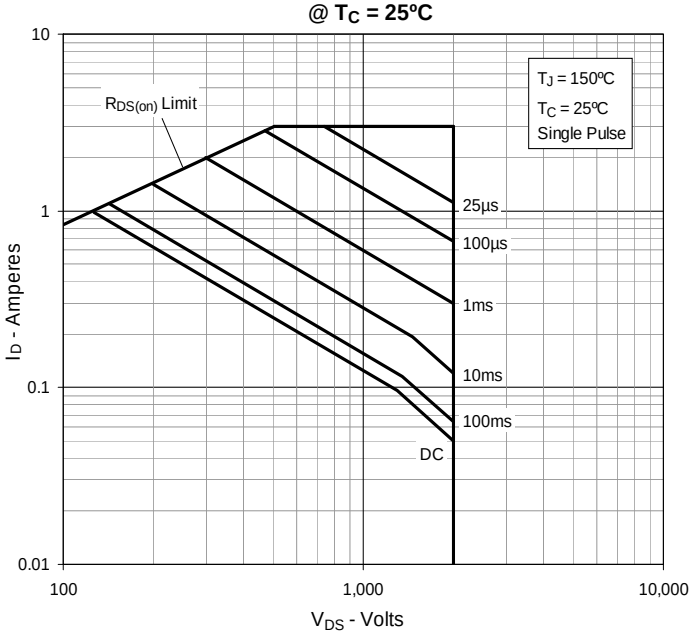


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 75ºC